

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	73244	HBT heterojunction (bipolar near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 15:05
L2	219944	(field near effect near transistor) FET mosfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 15:06
L3	28094	1 and 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 15:07
L16	477	3 and (InGaP GaInP)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/28 17:26